

WHAT IS CLAIMED IS:

1. A semiconductor device comprising an element isolation region formed at a main surface of a semiconductor substrate and a silicon nitride film formed on said element isolation region,
said element isolation region having an upper surface protruding
5 above said main surface of said semiconductor substrate, and
said silicon nitride film being positioned, as seen from above, inner than a portion of said element isolation region exposed on said main surface of said semiconductor substrate.
2. The semiconductor device according to claim 1, wherein said element isolation region is formed to fill a trench provided at said main surface of said semiconductor substrate, and said silicon nitride film is
5 positioned, as seen from above, to cover an area of said semiconductor substrate forming a bottom surface of said trench.
3. The semiconductor device according to claim 1, wherein, as seen from above, said silicon nitride film overlaps an element region that is formed adjacent to said element isolation region.